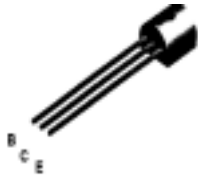

NPN TRANSISTOR**C945****100mA**



- AF OUTPUT AMPLIFIER

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS (Ta=25)

PARAMETERS	SYMBOL	MIN	TYP	MAX	UNIT	CONDITION
Collector-Emitter Breakdown Voltage	BV _{ceo}	50			V	I _c =1mA
Collector-Base Breakdown Voltage	BV _{cb0}	60			V	I _c =5 μ A
Emitter-Base Breakdown Voltage	BV _{eb0}	5			V	I _e =50 μ A
Collector-Base Leakage	I _{cbo}			0.1	μ A	V _{cb} =60V
Emitter-Base Leakage	I _{ebo}			0.1	μ A	V _{eb} =5V
Collector-Emitter Saturation Voltage	V _{ce (sat)}		0.18	0.3	V	I _c =100mA, I _b =10mA
DC Current Gain	H _{fe}	90	200	600		V _{ce} =6.0V, I _c =1.0mA
Collector Current	I _c		100		mA	
Current Gain Bandwidth	f _r	100	180		MHz	V _{ce} =6V, I _e =10mA
Output Capacitance	C _{ob}		4.5	6.0	pF	V _{cb} =10V, I _e =0, f=1MHz
Power Dissipation	P _c			0.25	W	
Junction Temperature	T _j			125		
Storage Temperature	T _{stg}	-55		125		

Classification of Hfe

Rank	R	Q	P	K
Range	90-180	135-270	200-400	300-600

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